EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	788	(257/E29.273).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/12/05 17:19
S99	1705	(257/72).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/12/05 17:18
\$20 8	333	(257/E29.294).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/12/05 15:07
\$20 7	131	S205 and (TFT thin adj film adj transistor) and grain near2 (boundaries boundary)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/05 15:06
S20 6	28	S205 and (SLS sequential adj lateral adj solidification)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/05 14:55
\$20 5	1080	438/158	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/05 14:55
\$20 4	252	S203 and display and (TFT thin adj film adj transistor) and grain adj (boundaries boundary)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/05 14:55
S20 3	1687	(257/66).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/12/05 14:47
\$20 2	32	(ul adj ho near3 lee).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/05 14:46
\$20 1	35	(hye adj dong near3 kim).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON .	2006/12/05 14:46
S20 0	65	(ji adj yong near3 park).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/05 14:45
S19 9	153	(jae adj bon near3 koo).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/05 14:45
S19 5	6	((poly adj Si polysilicon polycrystalline polycrystallization polycrystallizing recrystallized) near3 active and transistor and channel and grain adj (boundaries boundary) and display).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR .	ON	2006/12/05 14:45
S19 7	592	(driver driving) adj2 (TFT transistor) and (pixel switching) adj2 (TFT transistor) and channel and grain adj (boundaries boundary) and display	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/05 14:17

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S19 8		((driver driving) adj2 (TFT transistor) and (pixel switching) adj2 (TFT transistor) and channel and grain adj (boundaries boundary) and display).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR .	ON	2006/12/05 13:27
S19 6	164	(driver driving) adj2 (TFT transistor) and (pixel switching) adj2 (TFT transistor) and display and (polycrystalline polycrystallization polysilicon poly adj si polycrystallizing recrystalliz\$5) and channel and SLS	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/05 13:27
S19 4	445	(poly adj Si polysilicon polycrystalline polycrystallization polycrystallizing recrystallized) near3 active and transistor and channel and grain adj (boundaries boundary) and display	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/05 13:14
S19 3	56	S192 and (driver driving) near2 (TFT transistor) and switching near2 (TFT transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/05 13:11
\$13 9	1927	(driver driving) near2 (TFT transistor) and switching near2 (TFT transistor) and display and (polycrystalline polycrystallization polysilicon poly adj si polycrystallizing recrystalliz\$5) and channel	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/12/05 13:11
S19 2	1011	(257/88).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/12/05 13:08
S19 1	233	(257/75).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/12/05 13:06
S19 0	2432	(257/72).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/12/05 13:06
S18 9	370	(257/64).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/12/05 13:06

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